



JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

DFNWB3×3-8L Plastic-Encapsulate MOSFETS

CJBM3020 N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D
30 V	8.8mΩ@10V	20A
	15mΩ@4.5V	

DESCRIPTION

The CJBM3020 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications

FEATURES

- Battery switch
- Load switch
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

APPLICATIONS

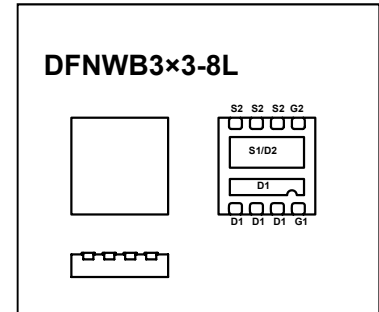
- SMPS and general purpose applications
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

MARKING

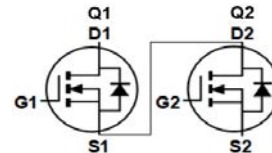
G2 S2 S2 S2



BM3020=Part No. Solid
dot=Pin1 indicator
XX=Code



EQUIVALENT CIRCUIT



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D^{(1)}$	20	A
Pulsed Drain Current	$I_{DM}^{(2)}$	80	A
Single Pulsed Avalanche Energy	$E_{AS}^{(3)}$	48	mJ
Power Dissipation	$P_D^{(1)}$	1.5	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}^{(6)}$	83.3	$^{\circ}\text{C/W}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D =250μA	30			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
On characteristics ④						
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	3.0	V
Static drain-source on-sate resistance	R _{DS(on)}	V _{GS} =10V, I _D =12A		8.8	14	mΩ
		V _{GS} =4.5V, I _D =10A		15	20	mΩ
Forward transconductance	g _{FS}	V _{DS} =5V, I _D =10A		20		S
Dynamic characteristics ④ ⑤						
Input capacitance	C _{iSS}	V _{DS} =15V,V _{GS} =0V, f =1MHz		999		pF
Output capacitance	C _{oSS}			145		
Reverse transfer capacitance	C _{rSS}			132		
Switching characteristics ④ ⑤						
Total gate charge	Q _g	V _{DS} =15V, V _{GS} =10V, I _D =14A		15		nC
Gate-source charge	Q _{gs}			2.6		
Gate-drain charge	Q _{gd}			5.3		
Turn-on delay time	t _{d(on)}	V _{DD} =15V,V _{GS} =10V, R _L =1.2Ω,R _{GEN} =3Ω		6.2		ns
Turn-on rise time	t _r			5.3		
Turn-off delay time	t _{d(off)}			43		
Turn-off fall time	t _f			7.1		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage	V _{SD} ④	V _{GS} =0V, I _S =10A			1.2	V
Continuous drain-source diode forward current	I _S ①				20	A

Notes:

1. $T_C=25^\circ\text{C}$ Limited only by maximum temperature allowed.

2. $PW \leq 10\mu s$, Duty cycle $\leq 1\%$.

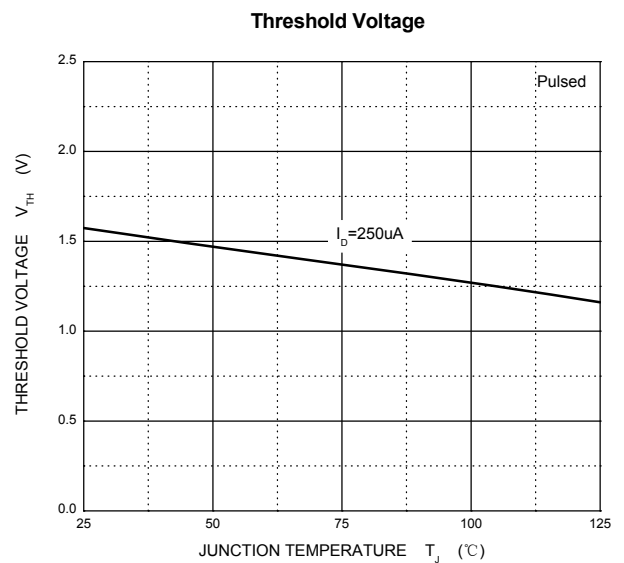
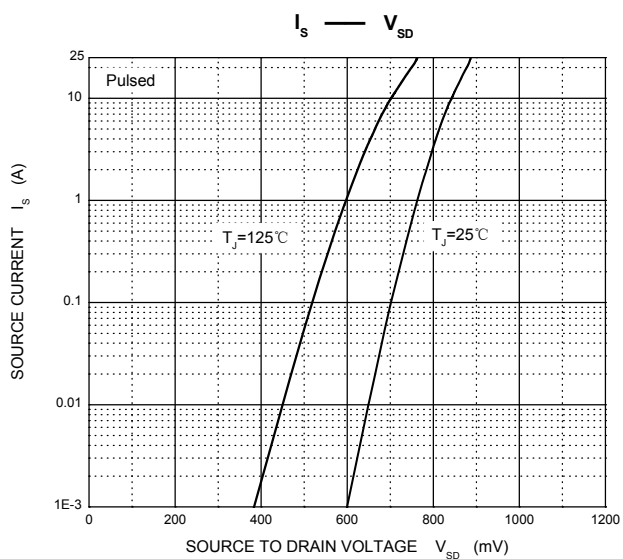
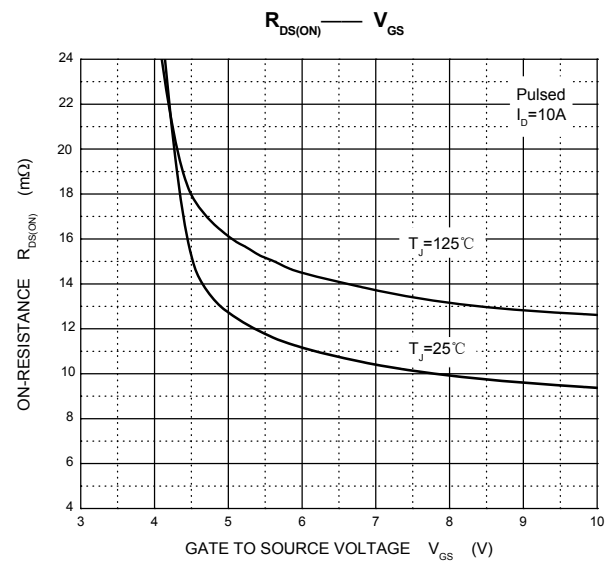
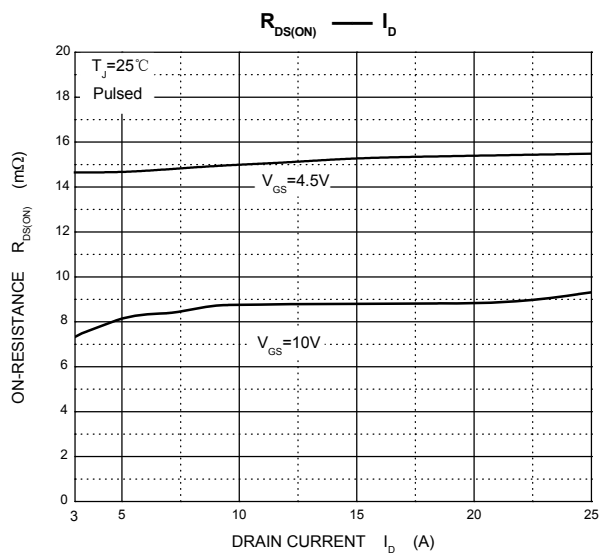
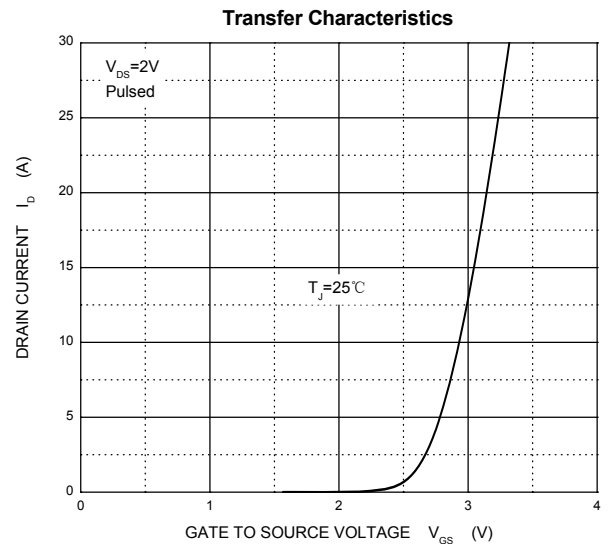
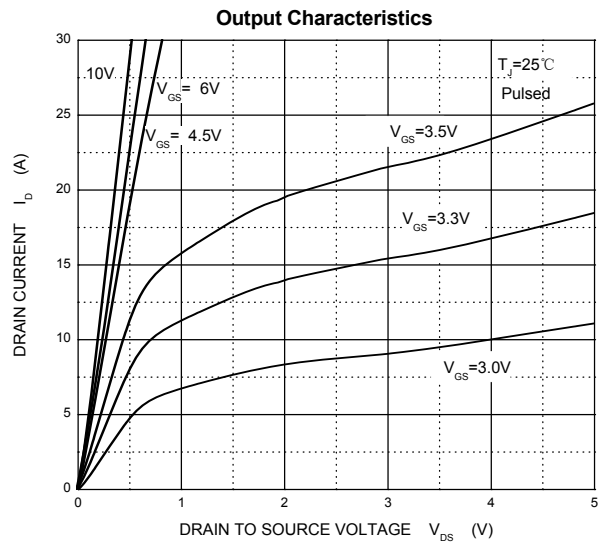
3. EAS condition: $V_{DD}=15V, V_{GS}=10V, L=0.1mH, R_g=25\Omega$ Starting $T_J = 25^\circ\text{C}$.

4. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.

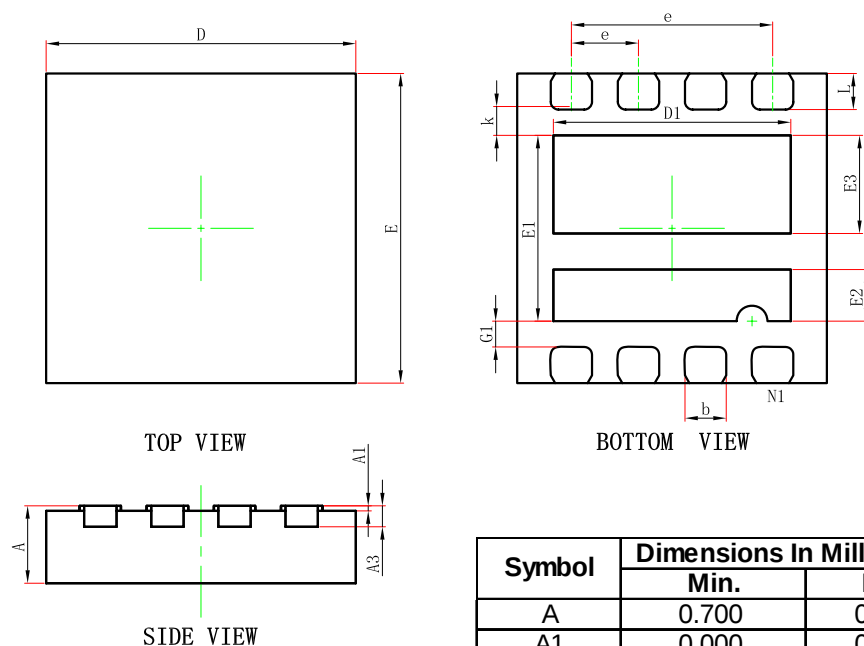
5. Guaranteed by design, not subject to production.

6. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25^\circ\text{C}$.

Typical Characteristics



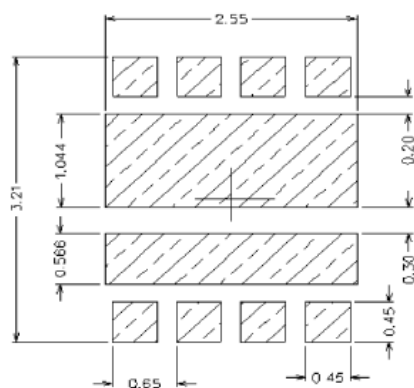
DFNWB3×3-8L-E Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	2.950	3.050	0.116	0.120
E	2.950	3.050	0.116	0.120
D1	2.250	2.350	0.089	0.093
E1	1.700	1.900	0.067	0.075
E2	0.450	0.550	0.018	0.022
E3	0.900	1.000	0.035	0.039
k	0.200	0.300	0.008	0.012
G1	0.200	0.300	0.008	0.012
b	0.350	0.450	0.014	0.018
e	0.650BSC		0.026BSC	
e1	1.95BSC		0.077BSC	
L	0.300	0.400	0.012	0.016

DFNWB3×3-8L Suggested Pad Layout

RECOMMENDED LAND PATTERN



Note:

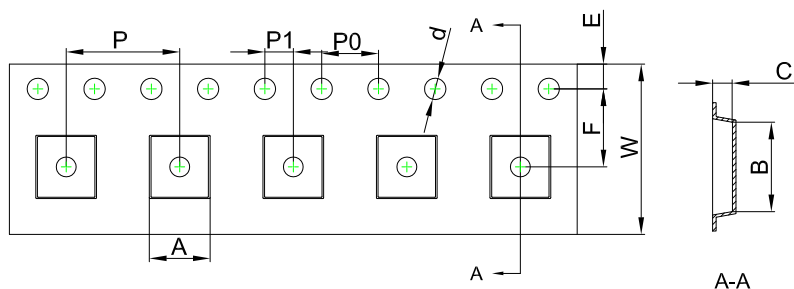
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.050\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

JSCJ reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

DFNWB3×3-8L Tape and Reel

DFNWB3×3-8L Embossed Carrier Tape

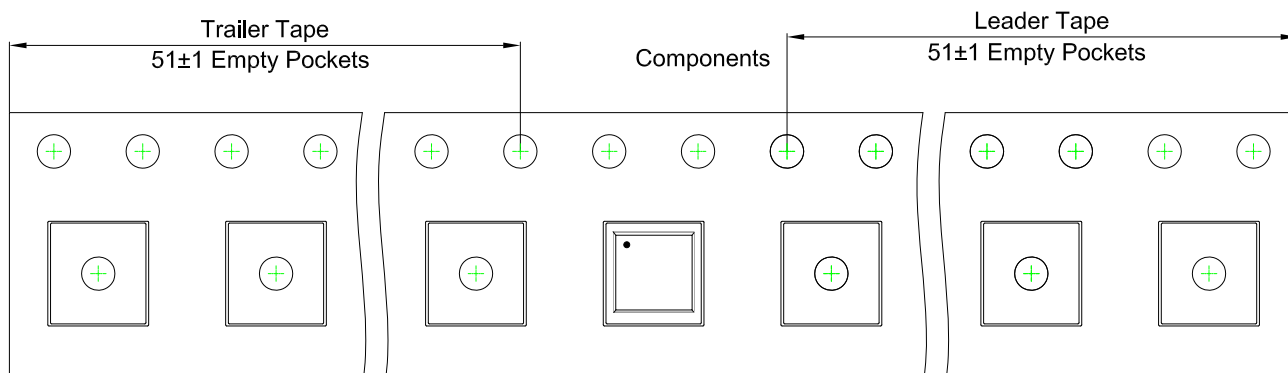


Packaging Description:

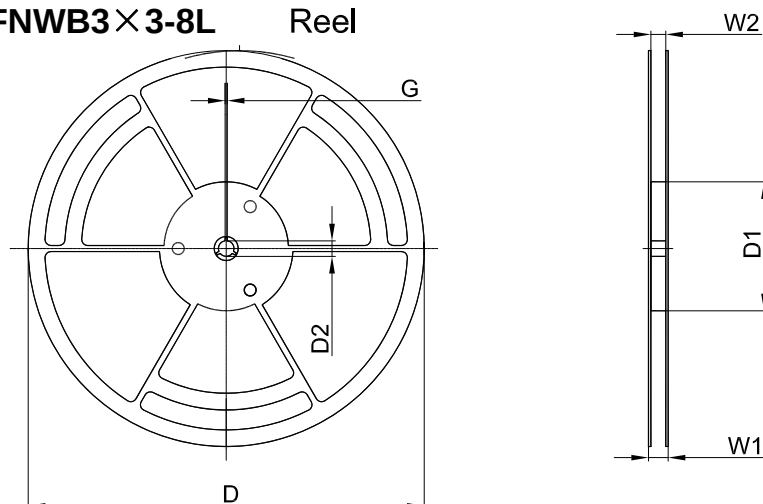
DFNWB3×3-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 5,000 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
DFNWB3×3-8L	3.55	3.55	1.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

DFNWB3×3-8L Tape Leader and Trailer



DFNWB3×3-8L Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	G	W1	W2
13"Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	5,000 pcs	340×336×29	50,000 pcs	353×346×365